FLAT-BASE TYPE INSULATED TYPE

#### PS11011



#### **INTEGRATED FUNCTIONS AND FEATURES**

- Converter bridge for 3 phase AC-to-DC power conversion.
- Circuit for dynamic braking of motor regenerative energy.
- 3-phase IGBT inverter bridge configured by the latest 3rd. generation IGBT and diode technology.
- Inverter output current capability Io (Note 1):

Type Name	100% load	150% over load		
PS11011	0.8A (rms)	1.2A (rms), 1min		

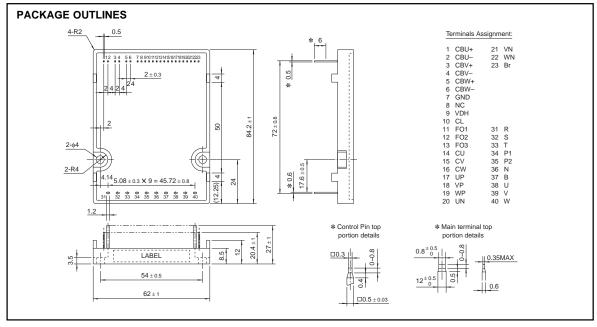
(Note 1) : The inverter output current is assumed to be sinusoidal and the peak current value of each of the above loading cases is defined as : IOP = IO  $\times \sqrt{2}$ 

#### INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS:

- For inverter side upper-leg IGBTs: Drive circuit, High voltage isolated high-speed level shifting, Short circuit protection (SC).
- Bootstrap circuit supply scheme (single drive power supply) and Under voltage protection (UV).
- For inverter side lower-leg IGBTs: Drive circuit, Short circuit protection (SC).
  - Control supply circuit under- & over- voltage protection (OV/UV).
  - System over temperature protection (OT). Fault output signaling circuit (Fo) and Current limit warning signal output (CL).
- For Brake circuit IGBT : Drive circuit
- · Warning and Fault signaling:
  - Fo1: Short circuit protection for lower-leg IGBTs and Input interlocking against spurious arm shoot-through.
  - Fo2: N-side control supply abnormality locking (OV/UV).
  - Fo3: System over-temperature protection (OT).
  - CL: Warning for inverter current overload condition
- For system feedback control : Analogue signal feedback reproducing actual inverter output phase currents (3\$).
- Input Interface : 5V CMOS/TTL compatible, Schmitt trigger input, and Arm-Shoot-Through interlock protection.

#### **APPLICATION**

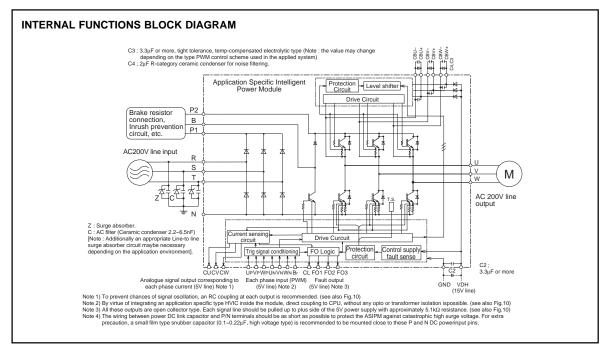
Acoustic noise-less 0.1kW/AC200V class 3 phase inverter and other motor control applications



(Fig. 1)



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(Fig. 2)

# MAXIMUM RATINGS (Tj = 25°C) INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P2-N	450	V
VCC(surge)	Supply voltage (surge)	Applied between P2-N, Surge-value	500	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
VP(S) or VN(S)	Each output IGBT collector-emitter switching surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	600	V
±IC(±ICP)	Each output IGBT collector current	Tc = 25°C	±2 (±4)	Α
IC(ICP)	Brake IGBT collector current	]	2 (4)	Α
IF(IFP)	Brake diode anode current	Note: "( )" means IC peak value	2 (4)	Α

#### **CONVERTER PART**

Symbol	Item	Condition	Ratings	Unit
VRRM	Repetitive peak reverse voltage		800	V
Ea	Recommended AC input voltage		220	V
lo	DC output current	3φ rectifying circuit	25	Α
IFSM	Surge (non-repetitive) forward current	1 cycle at 60Hz, peak value non-repetitive	138	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	Value for one cycle of surge current	80	A <sup>2</sup> s

#### **CONTROL PART**

Symbol	Item	Condition	Ratings	Unit
VDH, VDB	Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	20	>
VCIN	Input signal voltage	Applied between UP · VP · WP · UN · VN · WN · Br-GND	<b>−</b> 0.5 ~ 7.5	>
VFO	Fault output supply voltage	Applied between Fo1 · Fo2 · Fo3-GND	<b>−</b> 0.5 ~ 7	V
IFO	Fault output current	Sink current of F01 · F02 · F03	15	mA
VCL	Current-limit warning (CL) output voltage	Applied between CL-GND	<b>−</b> 0.5 ~ 7	V
ICL	CL output current	Sink current of CL	15	mA
Ico	Analogue current signal output current	Sink current of CU · CV · CW	±1	mA



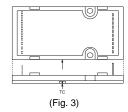
# FLAT-BASE TYPE INSULATED TYPE

# TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	<b>−</b> 20 ~ <b>+</b> 125	°C
Tstg	Storage temperature	_	<b>−</b> 40 ~ <b>+</b> 125	°C
Tc	Module case operating temperature	(Fig. 3)	<b>−20 ~ +100</b>	°C
Viso	Isolation voltage	60 Hz sinusoidal AC applied between all terminals and the base plate for 1 minute.	2500	Vrms
_	Mounting torque	Mounting screw: M3.5	0.78 ~ 1.27	kg-cm

Note 2) The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure junction temperature as high as 150°C instantaneously. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is requested to be provided before use.

# CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



# THERMAL RESISTANCE

Symbol	Item	Condition		Unit		
	nem		Min.	Тур.	Max.	Unit
Rth(j-c)Q		Inverter IGBT (1/6)	_	_	7.3	°C/W
Rth(j-c)F	Junction to case Thermal Resistance	Inverter FWDi (1/6)	_	_	6.1	°C/W
Rth(j-c)QB		Brake IGBT	_	_	7.3	°C/W
Rth(j-c)FB	resistance	Brake FWDi	_	_	6.1	°C/W
Rth(j-c)FR		Converter Di (1/6)	_	_	4.8	°C/W
Rth(c-f)	Contact Thermal Resistance	Case to fin, thermal grease applied (1 Module)	_		0.053	°C/W

# **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Symbol	Item	Condition	Ratings			Unit	
Symbol		Condition		Тур.	Max.	Unit	
VCE(sat)	Collector-emitter saturation voltage	VDH = VDB = 15V, Input = ON, Tj = 25°C, IC = 2A	_	_	2.9	V	
VEC	FWDi forward voltage	Tj = $25^{\circ}$ C, lc = $-2A$ , Input = OFF	_	_	2.9	V	
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	V <sub>DH</sub> = 15V, Input = ON, Tj = 25°C, IC = 2A	_	_	3.5	V	
VFBr	Brake diode forward voltage	Tj = 25°C, IF = 2A, Input = OFF	_	_	2.9	V	
IRRM	Converter diode reverse current	VR = VRRM, Tj = 125°C	_	_	8	mA	
VFR	Converter diode voltage	Tj = 25°C, IF = 5A	-	_	1.5	V	
ton		1/2 Bridge inductive load, Input = ON	0.3	0.6	1.5	μs	
tc(on)	Switching times	Vcc = 300V, Ic = 2A, Tj = 125°C	_	0.2	0.6	μs	
toff	Owitering times	VDH = 15V, VDB = 15V	_	1.1	1.8	μs	
tc(off)		Note : ton, toff include delay time of the internal control	_	0.35	1.0	μs	
trr	FWD reverse recovery time	circuit	_	0.1	_	μs	
	Short circuit endurance	Vcc ≤ 400V, Input = ON (one-shot)	No destruction				
	(Output, Arm, and Load,	Tj = 125°C start	• Fo output by protection operation			ration	
	Short Circuit Modes)	13.5V ≤ VDH = VDB ≤ 16.5V					
		Vcc ≤ 400V, Tj ≤ 125°C,	No dest	ruction			
	Switching SOA	Ic < IOL(CL) operation level, Input = ON	No protecting operation		ration		
		13.5V ≤ VDH = VDB ≤ 16.5V	No Fo output				



### **FLAT-BASE TYPE INSULATED TYPE**

#### **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, VDH = 15V, VDB = 15V unless otherwise noted)

Symbol	Item		Condition			Ratings		11.2
Cyrribor	item				Min.	Тур.	Max.	Unit
IDH	Circuit current		VDH = 15V, VCIN = 5V		-	_	150	mA
Vth(on)	Input on threshold voltage				0.8	1.4	2.0	V
Vth(off)	Input off threshold voltage				2.5	3.0	4.0	V
Ri	Input pull-up resistor		Integrated between inpu			150		kΩ
fPWM	PWM input frequency		Tc ≤ 100°C, Tj ≤ 125°C		2	_	20	kHz
txx	Allowable input on-pulse wi	dth	VDH = 15V, TC = −20°C	, ,	1	_	500	μs
tdead	Allowable input signal dead blocking arm shoot-through		Relates to corresponding (Except brake part) Tc =	•	2.2	_	_	μs
tint	Input inter-lock sensing		Relates to corresponding	input (Except brake part)		65	100	ns
Vco			Ic = 0A	VDH = 15V	1.87	2.27	2.57	V
Vc+(200%)	Analogue signal linearity wi	th	Ic = IOP(200%)	Tc = -20°C ~ +100°C	0.77	1.17	1.47	V
Vc-(200%)	output current		Ic = -Iop(200%)	(Fig. 4)	2.97	3.37	3.67	V
ΙΔVcοΙ	Offset change area vs temperature		VDH = 15V, Tc = -20°C	~ +100°C	-	15	_	mV
VC+	Analogue signal output valtage limit		Ic > IoP(200%), VDH = 15V		_	_	0.7	V
Vc-	Analogue signal output voltage limit		(Fig. 4)		4.0	_	_	V
ΔVc(200%)	Analogue signal over all linear variation		Vco-Vc±(200%)		_	1.1	_	V
гСН	Analogue signal data hold accuracy		Correspond to max. 50 only, Ic = IOP(200%)	0μs data hold period (Fig. 5)	-5	_	5	%
td(read)	Analogue signal reading tin	ne	After input signal trigge	r point (Fig. 8)	_	3	_	μs
±IOL	Current limit warning (CL) on	eration level	VDH =15V, TC = -20°C	~ +100°C (Note 4)	2.64	3.10	3.60	Α
ICL(H)	Signal output current of	Idle			_	_	1	μΑ
ICL(L)	CL operation	Active	Open collector output			1	_	mA
SC	Short circuit over current tri	p level	Tj = 25°C	(Fig. 7) (Note 5)	3.50	6.00	9.60	Α
ОТ		Trip level			100	110	120	∘c
OTr	Over temperature protection	Reset level	VDH =15V			90	_	°C
UVDH		Trip level			11.05	12.00	12.75	V
UVDHr		Reset level			11.55	12.50	13.25	V
OVDH		Trip level			18.00	19.20	20.15	V
OVDHr	Supply circuit under &	Reset level	$Tc = -20^{\circ}C \sim +100^{\circ}C$		16.50	17.50	18.65	V
UVDB	over voltage protection	Trip level	Tj ≤ 125°C		10.0	11.0	12.0	V
UVDBr		Reset level	1		10.5	11.5	12.5	V
tdV	Filter time		†		_	10	_	μs
IFO(H)		Idle			_	_	1	μA
IFO(L)	Fault output current	Active	Open collector output			1	<u> </u>	mA
J(L)		5.110						1117 (

(Note 3): (a) Allowable minimum input on-pulse width: This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width: This item applies to both P-side and N-side circuits excluding the brake circuit.

(Note4): CL output: The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The

circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5): The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momentarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

#### **RECOMMENDED CONDITIONS**

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied across P2-N terminals	400 (max.)	V
VDH, VDB	Control supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	15±1.5	V
$\Delta V$ DH, $\Delta V$ DB	Supply voltage ripple		±1 (max.)	V/µs
VCIN(on)	Input on voltage		0 ~ 0.3	V
VCIN(off)	Input off voltage		4.8 ~ 5.0	V
fPWM	PWM Input frequency	Using application circuit	2 ~ 20	kHz
tdead	Arm shoot-through blocking time	Using application circuit	2.2 (min.)	μs



FLAT-BASE TYPE INSULATED TYPE

Fig. 4 OUTPUT CURRENT ANALOGUE SIGNALING LINEARITY

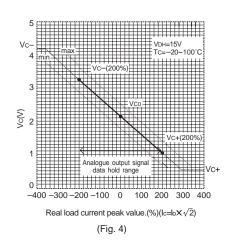
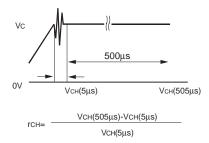
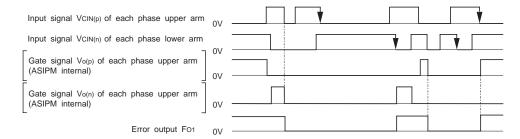


Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 µs delayed point.

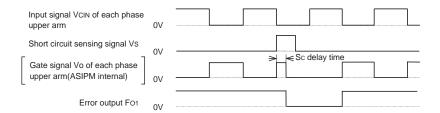
Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note: Input interlock protection circuit; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

#### Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION

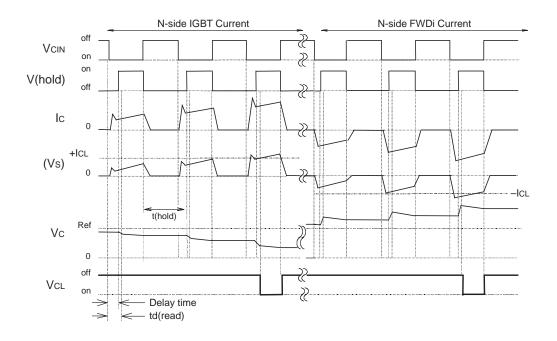


Note: Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").

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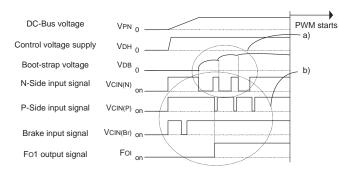
FLAT-BASE TYPE INSULATED TYPE

Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART

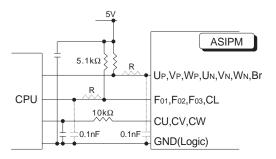


# Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to Supply voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph



# Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT



#### a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. 20μs number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

#### b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br  $\to$  Un/Vn/Wn  $\to$  Up/Vp/Wp in that order.

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